

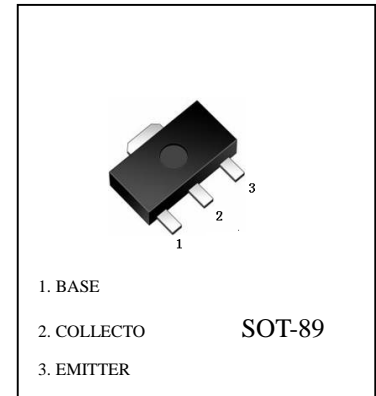
FEATURES

- Low voltage

2SC2883 (NPN)

Maximum Ratings (Ta=25 °C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	30	V
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current -Continuous	I _C	1.5	A
Collector Power dissipation	P _C	0.5	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55to +150	°C



ELECTRICAL CHARACTERISTICS (@ Ta=25 °C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CBO}	I _C =1mA, I _E =0	30			V
Collector-emitter breakdown voltage	V _{CEO}	I _C =10mA, I _B =0	30			V
Emitter-base breakdown voltage	V _{EBO}	I _E =1mA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =30V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =2V, I _C =0.5A	100		320	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =1.5A, I _B =30mA			2	V
Base-emitter voltage	V _{BE}	V _{CE} =2V, I _C =0.5A			1	V
Transition frequency	f _T	V _{CE} =2V, I _C =500mA		120		MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz			40	pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320
Marking	GO	GY



2SC2883 Typical Characteristics

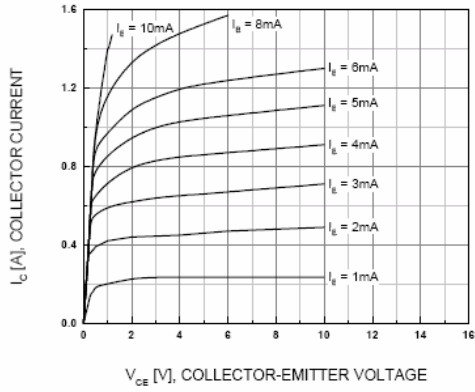


Figure 1. Static Characteristics

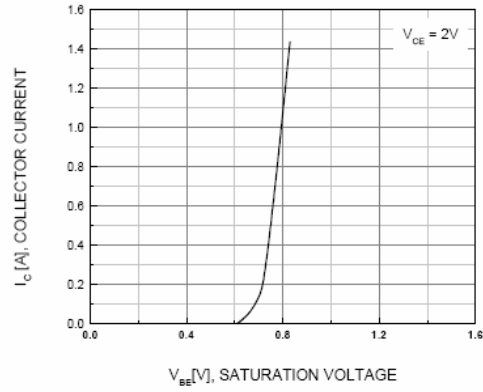


Figure 2. Base-Emitter On Voltage

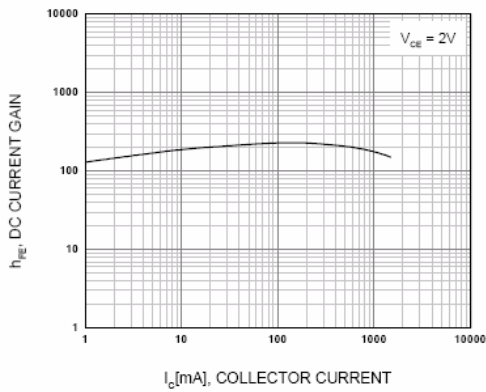


Figure 3. DC Current Gain

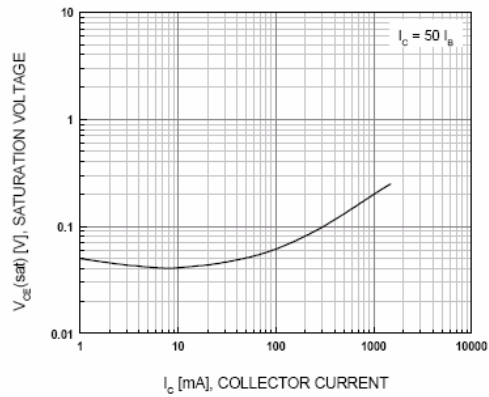


Figure 4. Collector-Emitter Saturation Voltage

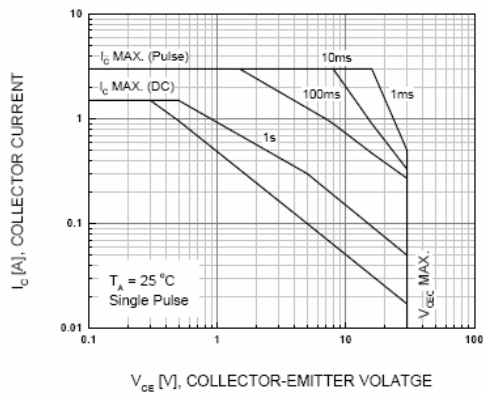


Figure 5. Safe Operating Area

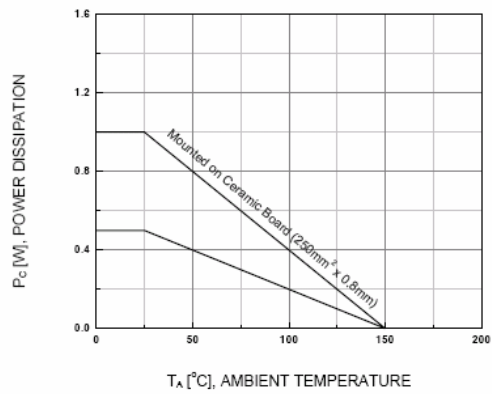


Figure 6. Power Derating